

<b>Notice of References Cited</b>	Application/Control No. 10/580,653	Applicant(s)/Patent Under Reexamination STOLZ ET AL.	
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**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
	B	US-			
	C	US-			
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**FOREIGN PATENT DOCUMENTS**

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**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
*	U	Ellmers et al., "GaAs-based VCSEL-structures with strain-compensated (GaIn)As/Ga(PAs)-MQWH active regions grown by using TBAs and TBP," Journal of Crystal Growth, 1998, Elsevier Science B.V., 195, p. 630-636
	V	
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